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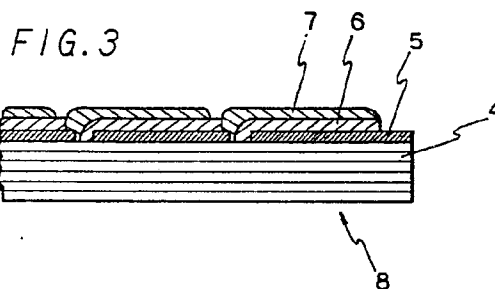
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## 54 Method for forming a thin film pattern.

57 A method for forming a thin film pattern comprising the steps in sequence of forming a lift-off layer (2) directly on a substrate (1) wherein a pattern of the lift-off layer is reverse to a desired thin film pattern, forming a thin film (3) on the substrate, removing an undesirable portion of the thin film (3) together with the lift-off layer (2); and a method for producing a semiconductor device (8) comprising the steps in sequence of forming a first electrode (5) on an insulated substrate (4), removing a part of the first electrode (5), forming a semiconductor including amorphous material (6) on the first electrode (5), forming a lift-off layer on the semiconductor including amorphous material at such a place whereon a second electrode is not desired to be formed,

and forming a second electrode (7) on the semiconductor.

According to the present invention, a thin film pattern can be formed at low production cost, with high productivity and accuracy, and with less danger during the process.





DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl. 4)
X	DE-A-2 420 394 (CANON K.K.)  * Page 5, last paragraph - page 14, paragraph 1; claims; figures *	1,2,4, 6,13, 14,17	H 01 L 31/18 H 01 L 31/02 H 01 L 21/00
X	--- US-A-4 489 101 (ULSI TECHNOLOGY RESEARCH) * Column 3, line 17 - column 4, line 66; claims; figures *	1,6,8, 14	
X	--- US-A-4 218 532 (BELL TELEPHONE LABORATORIES)  * Claims; figures 1-8 *	1,6,10 ,13,14 ,17	
X	--- US-A-4 497 684 (AMDAHL CORP.)  * Claims; figures *	1,6,10 ,13,14 ,17	TECHNICAL FIELDS SEARCHED (Int. Cl. 4)  H 01 L
E	--- EP-A-O 178 327 (NISSHA PRINTING CO.)  * Page 6, paragraph 1 - page 16, paragraph 1; claims; figures *	1,2,5, 6,13, 14,17	
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The present search report has been drawn up for all claims			
Place of search THE HAGUE		Date of completion of the search 16-10-1987	Examiner GORUN M.
CATEGORY OF CITED DOCUMENTS X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document			